DISCRETE SEMICONDUCTORS



Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 May 24



Philips Semiconductors

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack
- Also available with preformed leads for easy insertion.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BYM56A		_	200	v
	BYM56B		_	400	v
	BYM56C		_	600	v
	BYM56D		_	800	v
	BYM56E		_	1000	v
V _{RWM}	crest working reverse voltage				
	BYM56A		_	200	v
	BYM56B		_	400	v
	BYM56C		_	600	v
	BYM56D		_	800	v
	BYM56E		_	1000	v
V _R	continuous reverse voltage				
	BYM56A		_	200	v
	BYM56B		_	400	v
	BYM56C		-	600	v
	BYM56D		_	800	v
	BYM56E		_	1000	v
I _{F(AV)}	average forward current	$T_{tp} = 60 \ ^{\circ}C;$ lead length = 10 mm; averaged over any 20 ms period; see Figs 2 and 4	_	3.5	A
		T_{amb} = 65 °C; PCB mounting (see Fig.9); averaged over any 20 ms period; see Figs 3 and 4	-	1.4	A
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sinewave; $T_j = T_{j max}$ prior to surge; $V_R = V_{RRMmax}$	-	80	A

DESCRIPTION

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Rugged glass package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

MAM104

Fig.1 Simplified outline (SOD64) and symbol.



BYM56 series

BYM56 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
E _{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j max}$ prior to surge; inductive load switched off	_	20	mJ
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature	see Fig.5	-65	+175	°C

ELECTRICAL CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 3 \text{ A}; T_j = T_{j \text{ max}}; \text{see Fig.6}$	-	_	0.95	V
		I _F = 3 A; see Fig.6	-	-	1.15	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA				
	BYM56A		225	_	_	V
	BYM56B		450	-	-	V
	BYM56C		650	_	_	V
	BYM56D		900	_	_	V
	BYM56E		1100	-	_	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig.7	-	_	1	μA
		V _R = V _{RRMmax} ; T _j = 165 °C; see Fig.7	_	_	150	μA
t _{rr}	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig.10	_	3	_	μs
C _d	diode capacitance	$V_R = 0 V$; f = 1 MHz; see Fig.8	-	90	-	pF

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length = 10 mm	25	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	75	K/W

Note

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper ≥40 μm, see Fig.9. For more information please refer to the *"General Part of Handbook SC01"*.

BYM56 series

GRAPHICAL DATA







a = 1.57, $v_R = v_{RRMmax}$, o = 0.5. Device mounted as shown in Fig.9.

Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



as a function of reverse voltage.

BYM56 series



BYM56 series



BYM56 series

PACKAGE OUTLINE



LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
more of the limiting values r of the device at these or at a	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or nay cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification imiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.